

Axion Electrodynamics

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April 3, 2023



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Original Maxwell Equations

$$\nabla \cdot B = 0 \quad (1)$$

$$\nabla \times E = -\frac{\partial B}{\partial t} \quad (2)$$

$$\nabla \cdot E = 0 \quad (3)$$

$$\nabla \times B = \mu_0 \epsilon_0 \frac{\partial E}{\partial t} \quad (4)$$

Precisely,

$$\partial_\mu F^{\mu\nu} = 0 \quad (5)$$

In the Lagrangian formalism, the corresponding action is

$$S_0 = -\frac{1}{4\mu_0} \int d^4x F_{\mu\nu} F^{\mu\nu} = \int d^4x \left(\frac{\epsilon_0}{2} E^2 - \frac{1}{2\mu_0} B^2 \right) \quad (6)$$



Now we introduce the coupling term

$$S_\theta = \int d^4x \frac{\theta e^2}{4\pi^2 \hbar} \frac{1}{4} F_{\mu\nu} \tilde{F}^{\mu\nu} = -\frac{\theta e^2}{4\pi^2 \hbar c} \int d^4x E \cdot B \quad (7)$$

where the dual tensor $\tilde{F}^{\mu\nu} = \frac{1}{2} \epsilon^{\mu\nu\rho\sigma} F_{\rho\sigma}$.



EOM

In general, the action governing the electric and magnetic field is given by

$$S = \int d^4x \left(-\frac{1}{4} F_{\mu\nu} F^{\mu\nu} + \frac{e^2}{16\pi^2\hbar} \theta(x, t) F_{\mu\nu} \tilde{F}^{\mu\nu} \right) \quad (8)$$

The equation of motion from this action

$$\nabla \cdot E = -\frac{\alpha c}{\pi} \nabla \theta \cdot B \quad (9)$$

$$-\frac{1}{c^2} \frac{\partial E}{\partial t} + \nabla \times B = \frac{\alpha}{\pi c} (\dot{\theta} + \nabla \theta \times E) \quad (10)$$

$$\nabla \cdot B = 0 \quad (11)$$

$$\frac{\partial B}{\partial t} + \nabla \times E = 0 \quad (12)$$

where $\alpha = \frac{1}{4\pi\epsilon_0} \frac{e^2}{\hbar c}$ is the the fine structure constant.

Induced Charge

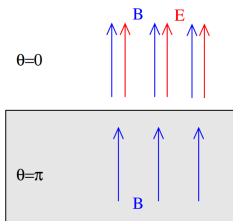


Figure 1: Applying a magnetic field

Consider a topological insulator with $\theta = \pi$ filling the lower half plane, $z < -\varepsilon$ and vacuum filling the upper half, $z > \varepsilon$. In the intermediate region $z \in [-\varepsilon, \varepsilon]$, $\partial_z \theta \neq 0$.

$$\nabla \cdot E = -\frac{\alpha c}{\pi} \nabla \theta \cdot B \quad (13)$$

$$= -\frac{\alpha c}{\pi} (\partial_z \theta) B \equiv \rho \quad (14)$$

The boundary of a topological insulator takes a magnetic field inside and generates an electric field outside.

Induced Current

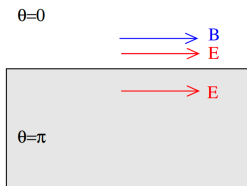


Figure 2: Applying an electric field

The electric field induces a surface current K perpendicular to E (Hall effect)

$$K_x = \alpha \epsilon_0 c E_y \quad (15)$$

and the Hall conductivity is

$$\sigma_{xy} = \frac{1}{2} \frac{e^2}{2\pi\hbar} \quad (16)$$



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Dirac Hamiltonian of a TI

$$\mathcal{H}_{TI}(k) = \hbar v_F k \cdot \alpha + m_0 \alpha_4 \quad (17)$$

The action of the systems in an external $A_\mu = (A_0, A)$ is^[1]

$$S_{TI} = \int d^4x \psi^\dagger \{ i(\partial_t - ieA_0) - [\mathcal{H}_{TI}(k + eA)] \} \psi \quad (18)$$

$$= \int d^4x \bar{\psi} [i\gamma^\mu (\partial_\mu - ieA_\mu) - m_0] \psi \quad (19)$$

$$\equiv iS_{TI}^E = \int d\tau d^3r \bar{\psi} [\gamma_\mu (\partial_\mu - ieA_\mu - m_0 e^{i\pi\gamma_5})] \quad (20)$$

where

- minimal coupling $k \rightarrow k + eA$.
- $\psi^\dagger \mathcal{H}_0 \psi \rightarrow \psi^\dagger (\mathcal{H}_0 - eA_0) \psi$
- $t \rightarrow -i\tau, A_0 \rightarrow iA_0, \gamma^j \rightarrow i\gamma_j$
- $m_0 = -m_0(\cos \pi + i\gamma_5 \sin \pi) = -m_0 e^{i\pi\gamma_5}$.



Fujikawa method

Consider an infinitesimal chiral transformation

$$\psi \rightarrow \psi' = e^{-i\pi d\phi \gamma_5/2} \psi \quad (21)$$

$$\bar{\psi} \rightarrow \bar{\psi}' = \bar{\psi} e^{-i\pi d\phi \gamma_5/2} \quad (22)$$

$$(23)$$

Then the partition function is transformed as

$$Z = \int \mathcal{D}[\psi \bar{\psi}] e^{-S_{TI}^E[\psi, \bar{\psi}]} \rightarrow Z' = \int \mathcal{D}[\psi' \bar{\psi}'] e^{-S_{TI}^E[\psi', \bar{\psi}']} \quad (24)$$

Due to the invariance of partition function, we arrive at

$$S_{TI}^E = \int d^4x \bar{\psi} [\gamma_\mu (\partial_\mu - ieA_\mu) - m_0] \psi + i \int d^4x \frac{\pi e^2}{32\pi^2 \hbar c} \epsilon^{\mu\nu\lambda\sigma} F_{\mu\nu} F_{\lambda\sigma} \quad (25)$$

where the θ term emerges.

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Hamiltonian of Two-node Weyl Semimetal

$$\mathcal{H}_0(k) = \hbar v_F (\tau_z k \cdot \sigma + b \cdot \sigma) \quad (26)$$

where τ_i and σ_i are Pauli matrix for Weyl nodes and spin degrees of freedom, $b \cdot \sigma$ represent spin-splitting term.

Using Fujikawa method, we obtain the action of the system^[1]

$$S = \int d^4x \bar{\psi} [i\gamma^\mu (\partial_\mu - ieA_\mu)] \psi + \frac{e^2}{2\pi^2 \hbar} \int d^4x b \cdot r E \cdot B \quad (27)$$

with $\theta(r, t) = 2b \cdot r$.

Nonzero and non-quantized θ always comes from the time-reversal symmetry breaking or inversion symmetry breaking.



Anomalous Hall Effect

The induced electric density and charge density with $\theta(r, t) = 2b \cdot r$ are given by

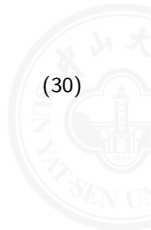
$$j(r, t) = \frac{e^2}{4\pi^2\hbar} [\dot{\theta}(r, t)B + \nabla\theta(r, t) \times E] = \frac{e^2}{2\pi^2\hbar} b \times E \quad (28)$$

Set $b = (0, 0, b), \Delta = 0,$

$$\mathcal{H}_{\pm}(k) = \hbar v_F(k_x\sigma_x + k_y\sigma_y) + m_{\pm}(k_z)\sigma_z = R(k) \cdot \sigma \quad (29)$$

where $m_{\pm}(k_z) = \hbar v_F(b \pm |k_z|)$. Hall conductivity

$$\sigma_{xy} = -\frac{e^2}{4\pi h} \int dk_x dk_y R \cdot \left(\frac{\partial R}{\partial k_x} \times \frac{\partial R}{\partial k_y} \right) = \frac{e^2}{2\pi^2\hbar} b \quad (30)$$



Reference

- [1] SEKINE A, NOMURA K. Axion electrodynamics in topological materials[J].
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Thank you!

